

TOSHIBA INTELLIGENT GTR MODULE SILICON N CHANNEL IGBT

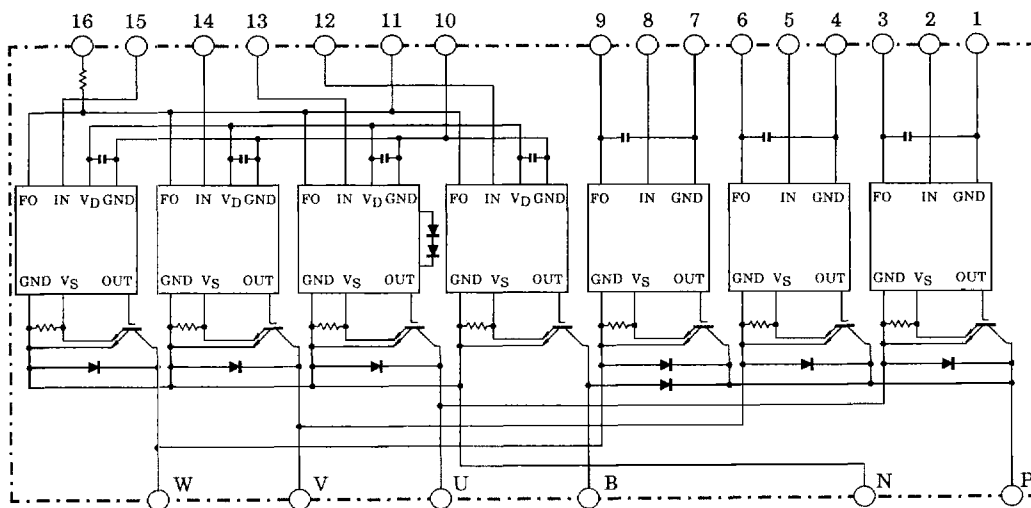
MIG75Q202H

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- Integrates Inverter, Brake Power Circuits & Control Circuits (IGBT drive units, Protection units for Over-Current, Realtime-Current-Control (RTC), Under-Voltage & Over-Temperature) in One Package.
- The Electrodes are Isolated from Case.
- High Speed Type IGBT : $V_{CE(sat)} = 3.5V$ (MAX.)
 $t_{off} = 2.8\mu s$ (MAX.)
 $t_{rr} = 0.21\mu s$ (MAX.)
- Outline TOSHIBA 2-110A1A
- Weight 520g

EQUIVALENT CIRCUIT



- | | | | | | |
|------------|------------|--------------|-------------|---------------|--------------|
| 1. GND (U) | 2. IN (U) | 3. V_D (U) | 4. GND (V) | 5. IN (V) | 6. V_D (V) |
| 7. GND (W) | 8. IN (W) | 9. V_D (W) | 10. GND (L) | 11. V_D (L) | 12. IN (B) |
| 13. IN (X) | 14. IN (Y) | 15. IN (Z) | 16. FO | | |

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MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$)

STAGE	CHARACTERISTIC	CONDITION	SYMBOL	RATINGS	UNIT
Inverter	Supply Voltage	P-N power terminal	V_{CC}	900	V
	Collector-Emitter Voltage	—	V_{CES}	1200	V
	Collector Current	$T_c = 25^\circ\text{C}$, DC	I_C	75	A
	Forward Current	$T_c = 25^\circ\text{C}$, DC	I_F	75	A
	Collector Power Dissipation	$T_c = 25^\circ\text{C}$	P_C	400	W
	Junction Temperature	—	T_j	150	$^\circ\text{C}$
Brake	Supply Voltage	P-N power terminal	V_{CC}	900	V
	Collector-Emitter Voltage	—	V_{CES}	1200	V
	Collector Current	$T_c = 25^\circ\text{C}$, DC	I_C	25	A
	Reverse Voltage	—	V_R	1200	V
	Forward Current	$T_c = 25^\circ\text{C}$, DC	I_F	25	A
	Collector Power Dissipation	$T_c = 25^\circ\text{C}$	P_C	140	W
	Junction Temperature	—	T_j	150	$^\circ\text{C}$
Control	Control Supply Voltage	V_D -GND terminal	V_D	20	V
	Input Voltage	IN-GND terminal	V_{IN}	20	V
	Fault Output Voltage	FO-GND (L) terminal	V_{FO}	20	V
	Fault Output Current	FO sink current	I_{FO}	10	mA
Module	Operating Temperature	—	T_C	$-20 \sim +100$	$^\circ\text{C}$
	Storage Temperature Range	—	T_{stg}	$-40 \sim +125$	$^\circ\text{C}$
	Isolation Voltage	AC 1 minute	V_{ISO}	2500	V
	Screw Torque	M5	—	3	Nm

ELECTRICAL CHARACTERISTICS

a. Inverter stage

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	I_{CEX}	$V_{CEX} = 1200\text{V}$	$T_j = 25^\circ\text{C}$	—	—	1	mA
			$T_j = 125^\circ\text{C}$	—	—	10	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_D = 15\text{V}$, $I_C = 75\text{A}$	$T_j = 25^\circ\text{C}$	—	2.6	3.5	V
		$V_{IN} = 15\text{V} \rightarrow 0\text{V}$	$T_j = 125^\circ\text{C}$	—	2.5	—	
Forward Voltage	V_F	$I_F = 75\text{A}$		—	2.2	3.0	V
Switching Time	t_{on}	$V_{CC} = 600\text{V}$, $I_C = 75\text{A}$ $V_D = 15\text{V}$, $V_{IN} = 15\text{V} \leftrightarrow 0\text{V}$ Inductive load (Note 1)			1.0	1.7	μs
	$t_c(\text{on})$				0.4	0.8	
	t_{rr}				0.16	0.21	
	t_{off}				1.9	2.6	
	$t_c(\text{off})$				0.35	0.6	

b. Brake stage

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	ICEX	V _{CEX} = 1200V	T _j = 25°C — T _j = 125°C —	— — —	1 10	mA
Collector-Emitter Saturation Voltage	V _{CE (sat)}	V _D = 15V, I _C = 25A V _{IN} = 15V → 0V	T _j = 25°C — T _j = 125°C —	2.6 2.5	3.5 —	V
Reverse Voltage	I _R	V _R = 1200V	T _j = 25°C — T _j = 125°C —	— —	1 10	mA
Forward Voltage	V _F	I _F = 25A	—	1.4	2.2	V
Switching Time	t _{on}	V _{CC} = 600V, I _C = 25A V _D = 15V, V _{IN} = 15V ↔ 0V Inductive load (Note 1)	—	1.3	1.9	μs
	t _{c (on)}		—	0.85	1.6	
	t _{rr}		—	0.42	0.50	
	t _{off}		—	1.9	2.6	
	t _{c (off)}		—	0.3	0.6	

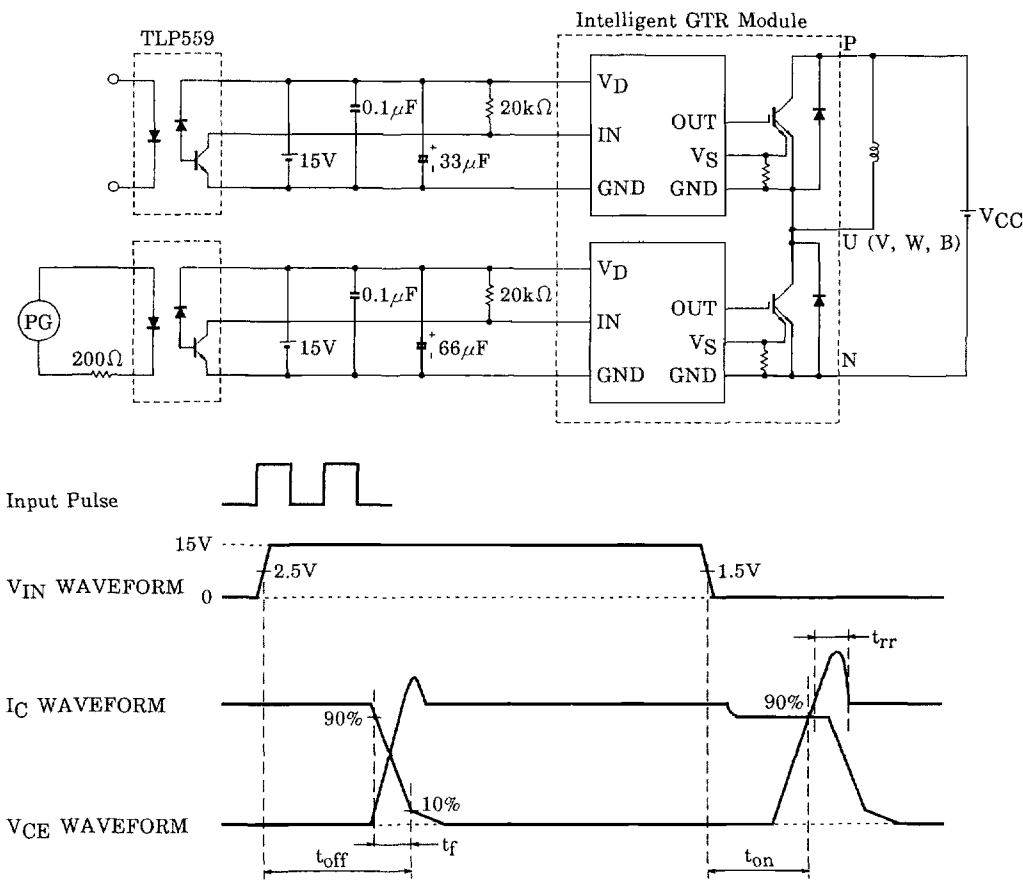
c. Control stage (T_j = 25°C)

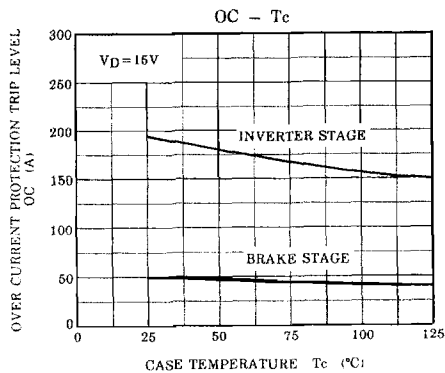
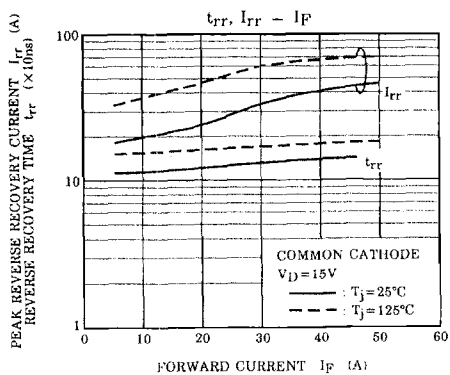
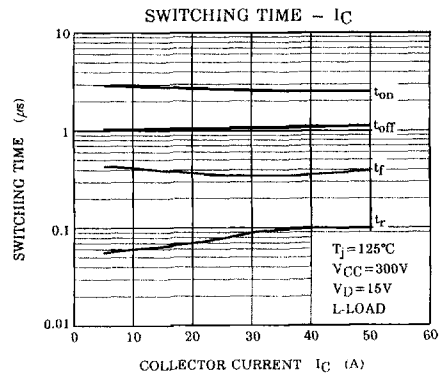
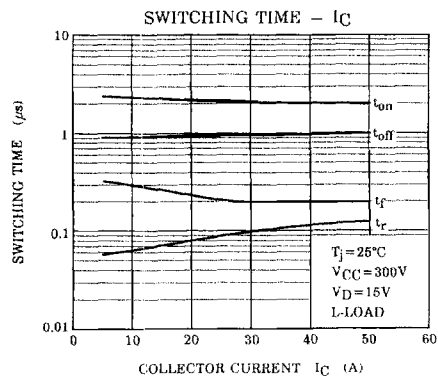
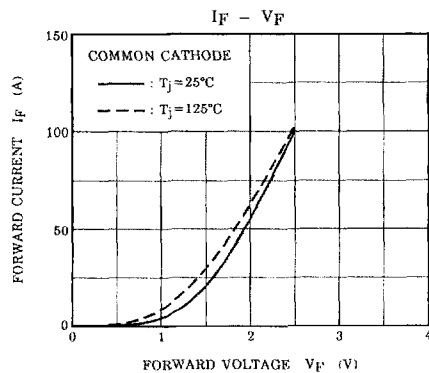
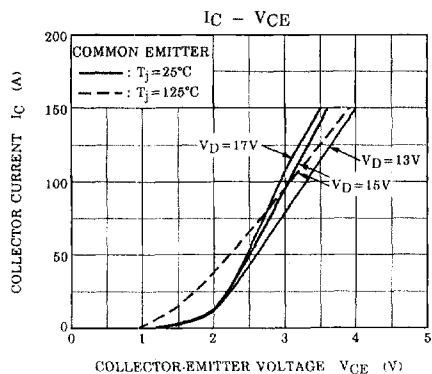
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Control Circuit Current	High Side	I _{D (H)}	V _D = 15V	8	12	mA
	Low Side	I _{D (L)}		32	48	
Input On Signal Voltage	V _{IN (on)}	V _D = 15V, I _C = 75mA	1.4	1.6	1.8	V
Input Off Signal Voltage	V _{IN (off)}	—	2.2	2.5	2.8	
Fault Output Current	Protection	I _{FO (on)}	V _D = 15V	5.4	6.0	mA
	Normal	I _{FO (off)}		—	0.1	
Over Current Protection Trip Level	Inverter	OC	V _D = 15V, T _j = 125°C	105	150	A
	Brake			85	100	
Short Circuit Protection Trip Level	Inverter	SC	V _D = 15V, T _j = 125°C	150	250	A
	Brake			120	150	
Over Current Cut-Off Time	t _{off (OC)}	V _D = 15V	—	5	—	μs
Over Temperature Protection	Trip Level	OT	Case temperature	110	118	°C
	Reset Level	OTr		—	98	
Control Supply Under Voltage Protection	Trip Level	UV	—	11.5	12.0	V
	Reset Level	UVr		12.0	12.5	
Fault Output Pulse Width	t _{FO}	V _D = 15V	1	2	3	ms

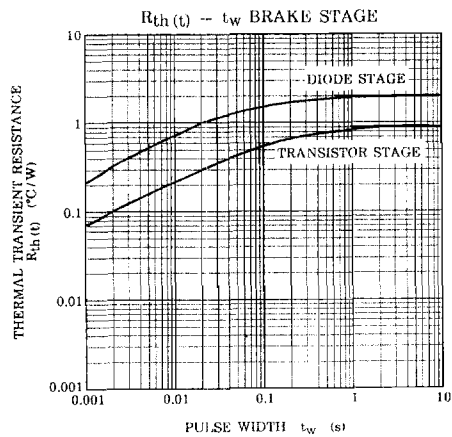
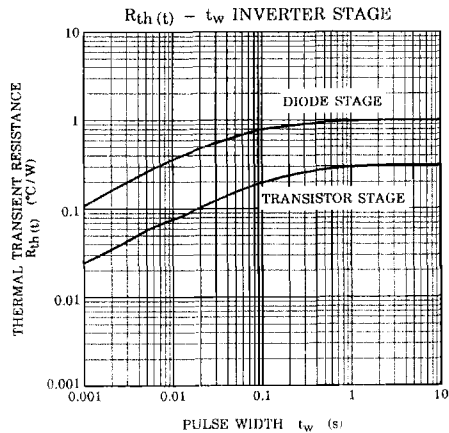
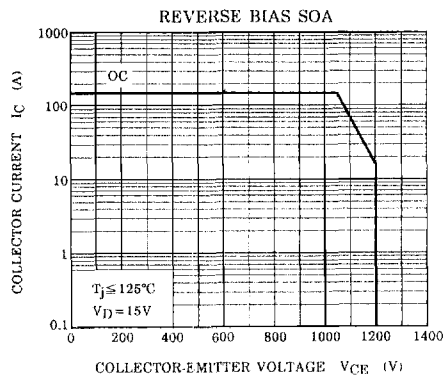
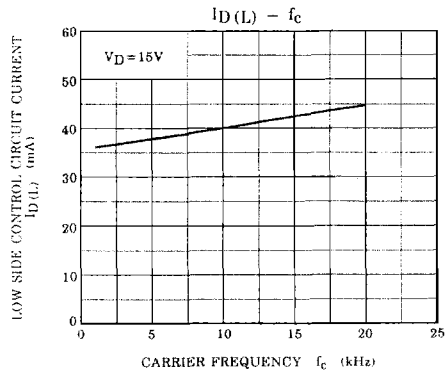
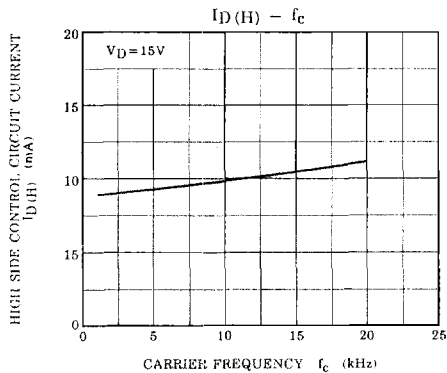
d. Thermal resistance ($T_j \approx 25^{\circ}\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Junction to Case Thermal Resistance	$R_{th(j-c)}$	Inverter IGBT stage	—	—	0.312	$^{\circ}\text{C/W}$
		Inverter FRD stage	—	—	1.00	
		Brake IGBT stage	—	—	0.892	
		Brake FRD stage	—	—	2.00	
Case to Fin Thermal Resistance	$R_{th(c-f)}$	Compound is applied	—	0.05	—	$^{\circ}\text{C/W}$

Note 1 : Switching time test circuit & timing chart







Unit : mm

